Measurements

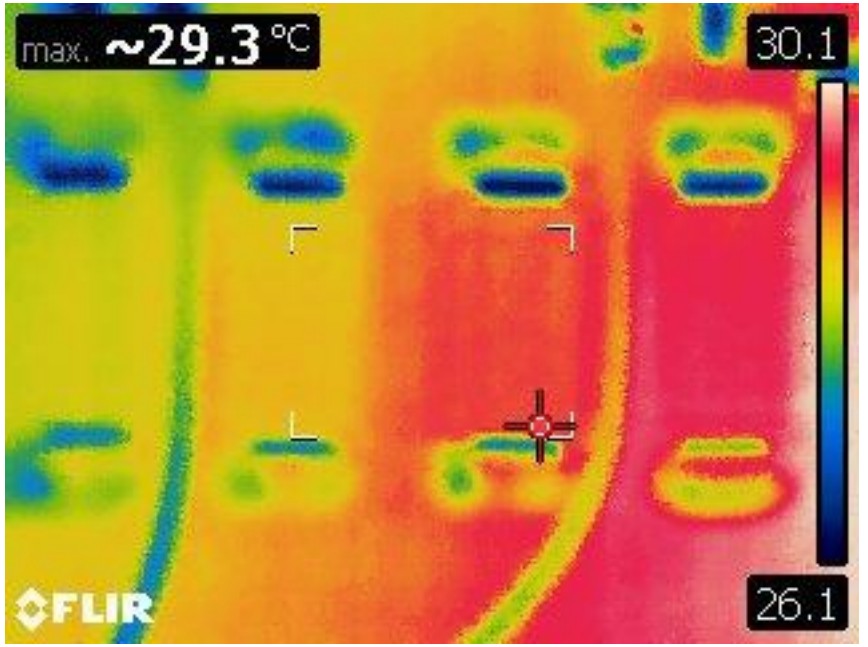
ON Semiconductor®

Measurements - 1

Discrete diode bridge not powered by PoE, far a way from heat source

Vbfd= 6.73mV @ 10V

Vbfd=47.2mV @ 57V



3P Reflected voltage over 100kΩ:

113mV and 123mV @ 10V

57V: 2.12V and 2.4V @ 57V

Perfectly OK for the existing backfeed voltage specification with huge margin:

0.0472V << 2.8V

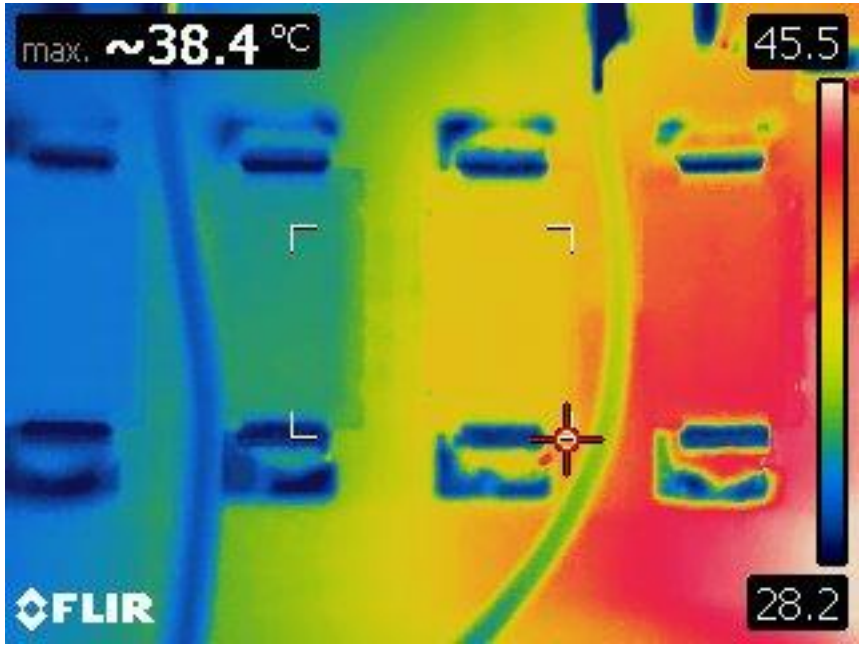
Coming close to the limit if 3P reflected voltage would be extended to a high voltage.

Measurements - 2

Discrete diode bridge not powered by PoE, closer to heat source

Vbfd= 7.65mV @ 10V

Vbfd=33.4mV @ 57V



3P Reflected voltage over 100kΩ:

108mV and 127mV @ 10V

2.4V and 3.34V @ 57V

Perfectly OK for the existing backfeed voltage specification with huge margin :

0.0334V << 2.8V

Would go above the limit if 3P reflected voltage would be extended to a high voltage.